

SPECIFICATION AMENDMENTS

Please replace paragraph [0001] with the following marked up version of this paragraph.

[0001] This application is a divisional application of U.S. Patent Application Serial No. 10/210,799 filed August 1, 2001, entitled "Semiconductor-Air Gap /Grating Fabrication Using a Sacrificial Layer Process", now U.S. Patent No. 6,649,439.

Please replace paragraph [0002] with the following marked up version of this paragraph.

[0002] This invention relates generally to semiconductor diffraction gratings and, more particularly, to a semiconductor structure that includes semiconductor epitaxial layers lattice matched to each other and ~~including~~ a diffraction grating therebetween, where the semiconductor layers and the diffraction grating material ~~having~~ have a greater difference in their indexes of refraction than the difference in the indexes of refraction of the semiconductor layers.